

	No.3260A	2SB1231/2SD1841 2SB1231 : PNP Epitaxial Planar Silicon Transistor 2SD1841 : NPN Triple Diffused Planar Silicon Transistor 100V/25A Switching Applications

Features

- Large current capacity and wide ASO.
- Low saturation voltage.

Applications

- Motor drivers, relay drivers, converters, and other general high-current switching applications

(): 2SB1231

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector-to-Base Voltage	V_{CB0}	(-)110	V
Collector-to-Emitter Voltage	V_{CEO}	(-)100	V
Emitter-to-Base Voltage	V_{EBO}	(-)6	V
Collector Current	I_C	(-)25	A
Collector Current(Pulse)	I_{CP}	(-)40	A
Base Current	I_B	(-)8	A
Collector Dissipation	P_C	3.0	W
		120	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

$T_c = 25^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

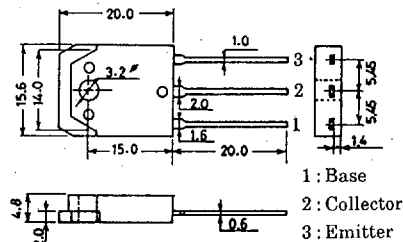
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)100\text{V}, I_E = 0$			(-)0.1	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)5\text{V}, I_C = 0$			(-)0.1	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = (-)2\text{V}, I_C = (-)2.5\text{A}$	50*		140*	
	$h_{FE(2)}$	$V_{CE} = (-)2\text{V}, I_C = (-)10\text{A}$	20			
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)10\text{A}, I_B = (-)1\text{A}$			(-)0.8	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)10\text{A}, I_B = (-)1\text{A}$			(-)1.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)1\text{mA}, I_E = 0$	(-)110			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)5\text{mA}, R_{BE} = \infty$	(-)100			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)1\text{mA}, I_C = 0$	(-)6			V

* : For the $h_{FE(1)}$ of the 2SB1231/2SD1841, specify at least two ranks in principle.

50 P 100	70 Q 140
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Package Dimensions 2022A

(unit : mm)



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